MSD6100

Dual Switching Diode Common Cathode

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_{R}	100	Vdc
Recurrent Peak Forward Current	lF	200	mAdc
Peak Forward Surge Current (Pulse Width = 10 μsec)	I _{FM(surge)}	500	mAdc
Total Device Dissipation @ T _A = 25°C (Note 1) Derate above = 25°C	P _D	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range (Note 1)	T _J , T _{stg}	-55 to +135	°C

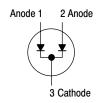
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

 Continuous package improvements have enhanced these guaranteed Maximum Ratings as follows: P_D = 1.0 W @ T_C = 25°C, Derate above 25°C – 8.0 mW/°C, T_J = -65 to +150°C, θJC = 125°C/W.



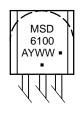
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



MSD6100 = Device Code

A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
MSD6100	TO-92	5000 Units / Box
MSD6100G	TO-92 (Pb-Free)	5000 Units / Box
MSD6100RLRA	TO-92	2000/Tape & Reel
MSD6100RLRAG	TO-92 (Pb-Free)	2000/Tape & Reel

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MSD6100

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) **(EACH DIODE)**

Characteristic	Symbol	Min	Max	Unit
Breakdown Voltage (I _(BR) = 100 μAdc)	V _(BR)	100	-	Vdc
Reverse Current	I _R	- - -	5.0 0.1 50	μAdc
Forward Voltage $ \begin{array}{l} (I_F=1.0 \text{ mAdc}) \\ (I_F=10 \text{ mAdc}) \\ (I_F=100 \text{ mAdc}) \end{array} $	V _F	0.55 0.67 0.75	0.7 0.82 1.1	Vdc
Capacitance (V _R = 0)	С	_	1.5	pF
Reverse Recovery Time ($I_F = I_R = 10 \text{ mAdc}$, $V_R = 5.0 \text{ Vdc}$, $i_{rr} = 1.0 \text{ mAdc}$)	t _{rr}	_	4.0	ns

TYPICAL CHARACTERISTICS

Curves Applicable to Each Anode

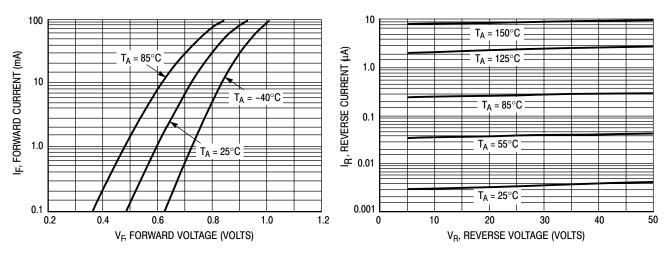


Figure 1. Forward Voltage

Figure 2. Leakage Current

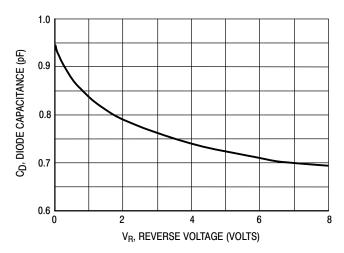
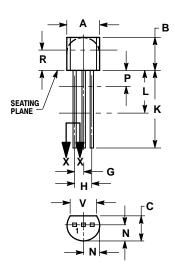


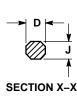
Figure 3. Capacitance

MSD6100

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 V14 5M 1982
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35	-	
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 3:

PIN 1. ANODE 2. ANODE 3. CATHODE

ON Semiconductor and was a registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.